

### - 20V Dual P-Channel Enhancement Mode MOSFET

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#### **Application Features** Notebook • • Fast switching Load Switch Green Device Available • Networking Suit for 1.5V Gate Drive Applications Hand-held Instruments Package and Pin Configuration **Circuit diagram** SOT363 **D1** D2 , S<sub>2</sub> D. ΚΩ **G1** G2 Marking: Top View S $D_2$ **S2** S **Top View** Pin out PIN1

#### Absolute Maximum Ratings Tc=25°C unless otherwise noted

Symbol	Parameter	Rating	Units
V <sub>DS</sub>	Drain-Source Voltage	-25	V
V <sub>GS</sub>	Gate-Source Voltage	±12	V
ID	Drain Current – Continuous (T <sub>c</sub> =25°C)	-1.1	А
I <sub>DM</sub>	Drain Current – Pulsed <sup>1</sup>	-2.2	A
D	Power Dissipation (T <sub>C</sub> =25°C)	280	mW
Po	Power Dissipation – Derate above 25°C	2.5	mW/°C
Т <sub>stg</sub>	Storage Temperature Range	-55 to 150	°C
TJ	Operating Junction Temperature Range	-55 to 150	°C

#### **Thermal Characteristics**

Symbol	Parameter	Тур.	Max.	Unit
Reja	Thermal Resistance Junction to ambient		350	°C/W



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#### **Electrical Characteristics (TJ=25** °C, unless otherwise noted)

Symbol	DI Parameter Conditions		Min.	Тур.	Max.	Unit
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V , I <sub>D</sub> =-250uA		-25		V
$\triangle BV_{DSS} / \triangle T_J$	BV <sub>DSS</sub> Temperature Coefficient	Reference to 25°C,I <sub>D</sub> =-1mA		-0.01		V/°C
1	Duraine Secure Looke as Current	V <sub>DS</sub> =-20V , V <sub>GS</sub> =0V , T <sub>J</sub> =25°C	1	/	-1	uA
IDSS	Drain-Source Leakage Current	V <sub>DS</sub> =-16V , V <sub>GS</sub> =0V , T <sub>J</sub> =125°C		(	-10	uA
I <sub>GSS</sub>	Gate-Source Leakage Current	$V_{GS}=\pm 12V$ , $V_{DS}=0V$			±20	uA

#### **On Characteristics**

		V <sub>GS</sub> =-4.5V , I <sub>D</sub> =-0.5A		400		
		V <sub>GS</sub> =-2.5V , I <sub>D</sub> =-0.5A		550	680	
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance	V <sub>GS</sub> =-1.8V , I <sub>D</sub> =-0.1A		750	1050	mΩ
V <sub>GS(th)</sub>	Gate Threshold Voltage		-0.5	-0.7	1.0	V
$ riangle V_{GS(th)}$	V <sub>GS(th)</sub> Temperature Coefficient	$V_{GS}=V_{DS}$ , $I_D = -250 uA$		3		mV/°C

#### Dynamic and switching Characteristics

Qg	Total Gate Charge <sup>2,3</sup>		 0.5	
Q <sub>gs</sub>	Gate-Source Charge <sup>2,3</sup>	V <sub>DS</sub> =10V , V <sub>GS</sub> =-4.5V , I <sub>D</sub> =-1A	 0.28	nC
$Q_gd$	Gate-Drain Charge <sup>2,3</sup>		 0.28	
T <sub>d(on)</sub>	Turn-On Delay Time <sup>2 , 3</sup>		 0.4	
Tr	Rise Time <sup>2,3</sup>	$V_{DD}$ =-10V , $V_{GS}$ =-4.5V , $R_{G}$ =6 $\Omega$	 0.06	
T <sub>d(off)</sub>	Turn-Off Delay Time <sup>2,3</sup>	I <sub>D</sub> =-1A	 0.02	ns
T <sub>f</sub>	Fall Time <sup>2,3</sup>		 0.8	
Ciss	Input Capacitance		 55	
Coss	Output Capacitance	$V_{DS}$ =-10V , $V_{GS}$ =0V , F=1MHz	 6	pF
C <sub>rss</sub>	Reverse Transfer Capacitance		 4.5	

#### **Drain-Source Diode Characteristics and Maximum Ratings**

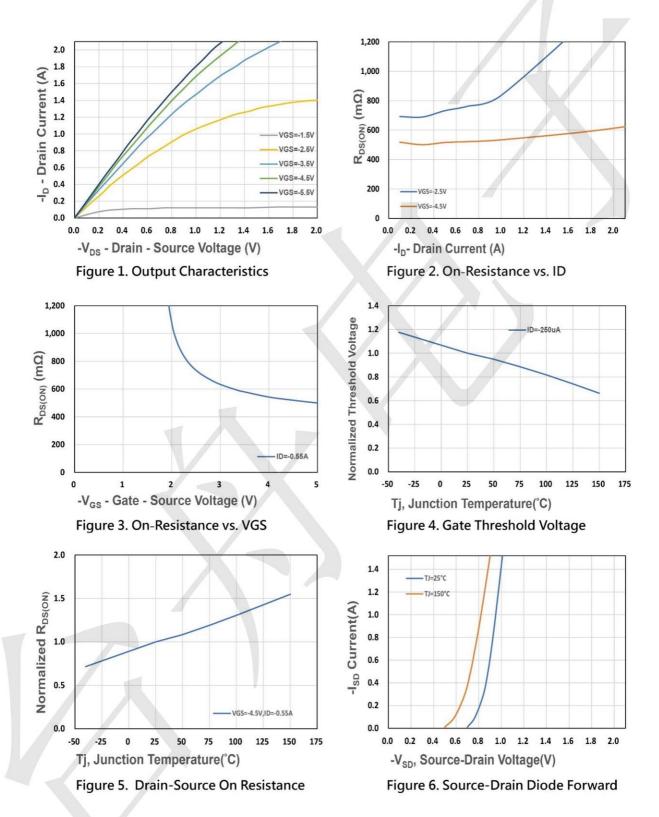
Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
V <sub>SD</sub>	Diode Forward Voltage	$V_{GS}{=}0V$ , $I_{S}{=}{-}0.2A$ , $T_{J}{=}25^{\circ}C$		-0.75	-1.1	V



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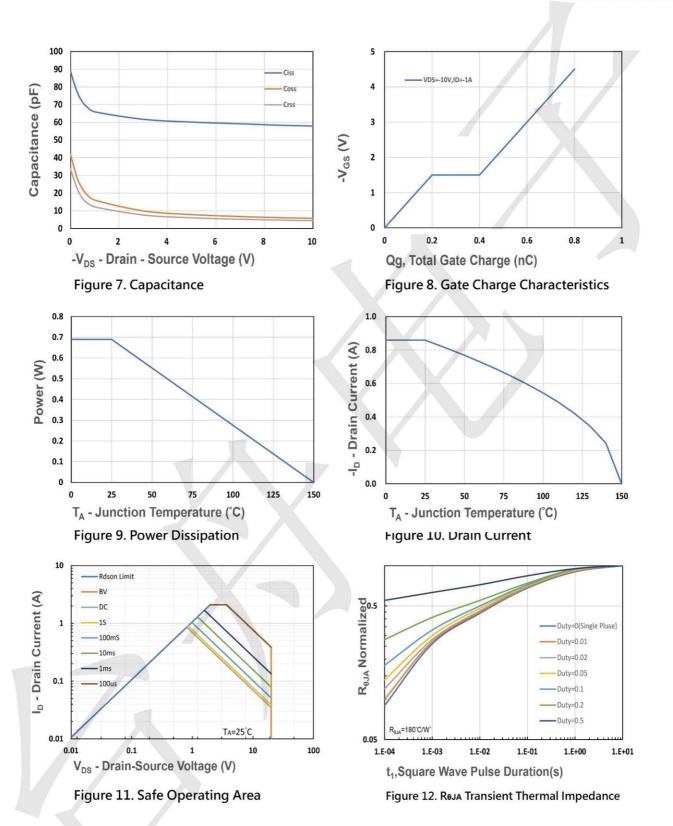
### **Characteristic Curves**





# TPM4152PEC6-1 - 20V Dual P-Channel Enhancement Mode MOSFET

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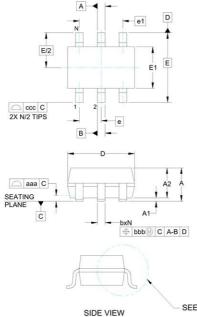




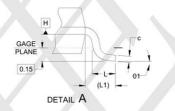
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## Outline Drawing - SOT-363(2.0X2.1)

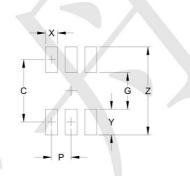


		DIM	IENSI	ONS			
DIM	I	NCHE	S	MILLIMETERS			
	MIN	NOM	MAX	MIN	NOM	MAX	
A	-	-	.043	-	-	1.10	
A1	.000	-	.004	0.00	-	0.10	
A2	.028	.035	.039	0.70	0.90	1.00	
b	.006	-	.012	0.15	-	0.30	
С	.003	-	.009	0.08		0.22	
D	.071	.079	.087	1.80	2.00	2.20	
E1	.045	.049	.053	1.15	1.25	1.35	
Е		083 BS	С	2	.10 BS	С	
е		026 BS	С	C	.65 BS	С	
e1		.051		1	.30 BS	С	
L	.010	.014	.018	0.26	0.36	0.46	
L1		(.017)			(0.42)		
Ν		6			6		
01	0°	8	8°	0°		8°	
aaa		.004	2		0.10		
bbb		.004			0.10		
CCC		.012	( )		0.30		



SEE DETAIL A

Land Pattern - SOT-363



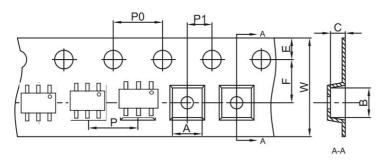
	DIMENSIONS										
DIM	INCHES	MILLIMETERS									
С	(.073)	(1.85)									
G	.039	1.00									
P	.026	0.65									
X	.016	0.40									
Y	.033	0.85									
Z	.106	2.70									



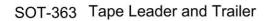
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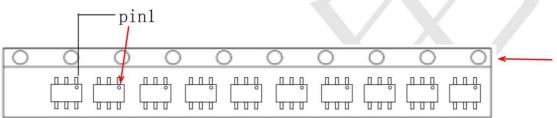
#### SOT-363 Embossed Carrier Tape



				Dimensions a	ire in millime	ter	_	-		
Pkg type	A	В	С	d	E	F	P0	Р	P1	W
SOT-363	2.25	2.55	1.20	Ø1.50	1.75	3.50	4.00	4.00	2.00	8.00

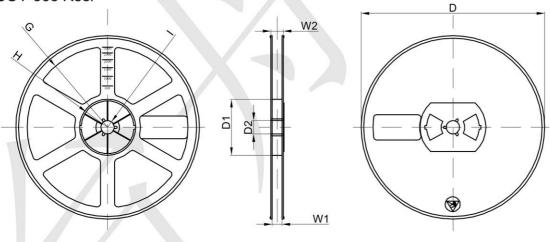


Package orientation in reel



Shipping: 3000pcs / Tape & Reel

#### SOT-363 Reel



	Dimensions are in millimeter											
Reel Option	D	D1	D2	G	н	I	W1	W2				
7"Dia	Ø178.00	54.40	13.00	R78.00	R25.60	R6.50	9.50	12.30				

	REEL	Reel Size	Box	Box Size(mm)	Carton	Carton Size(mm)	G.W.(kg)
;	3000 pcs	7 inch	45,000 pcs	203×203×195	180,000 pcs	438×438×220	

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